L Numb r	Hits	Search Text	DB	Time stamp
1	26645	355/$.c ls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/10 12:08
2	102	430/13.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/10 12:09
3	435	257/620.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/10 12:09
-	1006	235/494.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:55
-	0	235/494.ccls. and chiba.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:56
-	0	jp-223380-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:56
-	9	"223380"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:57
-	0	jp-223380-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:58
-	0	jp-5923512-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:58
-	2	jp-2000223380-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00

-	0	jp-2175154-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00
-	1	jp-3116919-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00
-	15423	chiba.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:02
-	818	chiba.in. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:02
-	58	(chiba.in. and semiconductor) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:05
-	153	(chiba.in. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:06
-	83	235/494.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:10
-	8	(235/494.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:06
-	34	(235/494.ccls. and semiconductor) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:47
-	2	6305677.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:16

-	174	269/13.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:18
-	81423	semic ndu tor adj2 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:19
-	4744	(semiconductor adj2 wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:19
-	4500	((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:20
-	61	(((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
-	22	semiconductor adj mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:52
-	1602	355/53.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	1154	355/53.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	1052	(355/53.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	415	((355/53.ccls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:30

-		8	(((355/53.c ls. and semiconductor) and wafer) and mark) and repr duce	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:32
-		0	(((355/53.ccls. and semic nduct r) and wafer) and mark) and efface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:32
-		5	(((355/53.ccls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:34
-		0	(((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce adj erased adj marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
-		0	((((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)) and efface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
-		10	((((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)) and notch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
-		300	(((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:38
-		0	(((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce near erased near marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:39
-		0	(((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce same erased same marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:39
-		121	(((355/53.ccls. and semiconductor) and wafer) and mark) and identical	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:40

-	9	((((355/53. cls. and semi nduct r) and wafer) and mark) and identical) and reprodu $2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:44
-	172	(((355/53.ccls. and s miconduct r) and wafer) and mark) and prevent	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:44
-	3	(((((355/53.ccls. and semiconductor) and wafer) and mark) and prevent) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
-	354	355/43.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
-	84	355/43.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
-	71	(355/43.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
-	1	(((355/43.ccls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:54
-	45	((355/43.ccls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:58
-	25968	355/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:58
-	2116	355/$.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59

-	1469	(355/$.ccls. and s mic nduct r) and waf r	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
-	497	((355/$. cls. and semi ndu t r) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
-	8	(((355/$.ccls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
-	13	(((355/$.ccls. and semiconductor) and wafer) and mark) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 19:02
-	1	((((355/$.ccls. and semiconductor) and wafer) and mark) and erase) and ((((355/$.ccls. and semiconductor) and wafer) and mark) and reproduce)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 19:02
-	6	(235/494.ccls. and semiconductor) and mark and duplicate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:51
-	0	(235/494.ccls. and semiconductor) and (duplicate adj mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:51
-	3	(235/494.ccls. and semiconductor) and (duplicate same mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:51
-	0	(semiconductor adj mark) same duplicate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
-	0	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and r produce) and (dupli ate same mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53

-	0	((((s mic ndu tor adj2 wafer) and mark) and (semic ndu t r adj waf r)) and repr duc) and (duplicate near mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
-	0	((((mic nductor adj2 waf r) and mark) and (semiconductor adj wafer)) and reproduce) and (duplicate adj mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
-	72	(((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:54
-	3	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce) and duplicate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:54